

A microscopic model for exchange bias

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Abstract

The domain state model for exchange bias has been further investigated by considering vector spins for the antiferromagnet instead of Ising spins used in the earlier studies. The qualitative results are similar to those with infinite anisotropy for the antiferromagnet. However, under certain conditions softer spins can lead to an even stronger bias field. The study shows a nontrivial dependence of the exchange bias on the antiferromagnetic anisotropy.

Keywords: Exchange biasing, Domain structure, Dilute antiferromagnet, Heisenberg antiferromagnet

The shift of the hysteresis loop along the field axis in a system containing a ferromagnet(FM)-antiferromagnet(AFM) interface is known as exchange bias (EB). The discovery of this effect by Meiklejohn and Bean in Co-CoO system [1] dates back to 1956. Subsequently the effect was observed in a variety of different

materials (see [2] for a review). There have been several approaches towards a theoretical understanding of the phenomenon and numerous different mechanisms are believed to be responsible for the shift. Malozemoff [3] explained the shift as a result of interface roughness. Koon considered a spin-flop coupling between the FM and the compensated AFM interface as responsible for the effect [4]. However, Schulthess and Butler argued that the spin-flop coupling alone cannot account for the effect [5] but an interface coupling through uncompensated defects together with the perpendicular coupling could explain the mechanism [6].

Recently a model was proposed [7] where the cause of the shift was attributed to the extra exchange field provided by the remanent magnetization of the domains in a diluted AFM. The model explained successfully several aspects related to the effect. The essential idea behind the model is that when the diluted AFM is cooled below the Néel temperature in presence of a field, it ends up in a domain state as opposed to long range order. These domains are metastable since the domain walls require large thermal fluctuations for any subsequent movement. The AFM is diluted by replacing its atoms by nonmagnetic impurities (e.g. $\text{Co}_{1-x}\text{Mg}_x\text{O}$). The domains are usually pinned at the impurity sites because at those sites it does not cost any energy for the creation of a domain wall. These domains carry a remanent magnetization [8, 9, 10] which provides the biasing field to the FM causing the shift of the hysteresis loop. Several issues related to EB, such as temperature dependence, training effect [11], role of AFM thickness [12] and, of course, the dependence of dilution on EB have been successfully explained within the framework of this model. In the earlier work [7, 11, 12], owing to the strong uniaxial anisotropy of CoO, the AFM was described by an Ising model. In the present work, we relax this restriction on the AFM. In order to investigate a broad class of systems for the AFM a Heisenberg model with

variable uniaxial anisotropy is considered.

The system we will study consists of one monolayer of FM and t monolayers of AFM. A certain fraction p of the AFM sites are left without a spin. The FM is exchange coupled to the topmost layer of the AFM. The Hamiltonian is thus given by

$$\begin{aligned}\mathcal{H} = & -J_{\text{FM}} \sum_{\langle i,j \rangle} \vec{S}_i \cdot \vec{S}_j - \sum_i \left(d_z S_{iz}^2 + d_x S_{ix}^2 + \vec{S}_i \cdot \vec{B} \right) \\ & -J_{\text{AFM}} \sum_{\langle i,j \rangle} \epsilon_i \epsilon_j \vec{\sigma}_i \cdot \vec{\sigma}_j - \sum_i \epsilon_i \left(k_z \sigma_{iz}^2 + \vec{\sigma}_i \cdot \vec{B} \right) \\ & -J_{\text{INT}} \sum_{\langle i,j \rangle} \epsilon_j \vec{S}_i \cdot \vec{\sigma}_j\end{aligned}$$

where $\vec{S}_i$ and $\vec{\sigma}_i$ denote spins at the i th site corresponding to FM and AFM respectively. The first line of the Hamiltonian describes the contribution to the energy coming from the FM with the z -axis as its easy axis ($d_z > 0$) and the x -axis as its hard axis ($d_x < 0$). The in-plane anisotropy keeps the FM preferentially in the $y - z$ plane. The second line is the contribution from the AFM with quenched disorder ($\epsilon_i = 0, 1$) also having its easy axis along z ($k_z > 0$). The last term describes the interaction of the FM with the interface AFM monolayer. The whole system is placed in an external magnetic field $\vec{B} = B\hat{z}$. In our simulations we set $J_{\text{FM}} = -2J_{\text{AFM}} = 2J_{\text{INT}}$.

We use Monte Carlo methods with a heat bath algorithm. Each spin is at every Monte Carlo step subject to a trial step consisting of a small deviation from the original direction followed by a total flip. This two-fold trial step can take care of a broad range of anisotropies starting from very soft spins up to the Ising limit [13]. The lateral dimension of the system was chosen in such a way that multiple AFM domains can be observed which is the case for a lattice size

$128 \times 128 \times (t+1)$. Starting from a temperature above the Néel temperature (T_N) of the diluted AFM but below the Curie temperature (T_c) of the FM, the system is cooled below T_N in presence of an external magnetic field $\vec{B} = 0.25J_{\text{FM}}\hat{z}$. Then the hysteresis curve of the system is calculated along the $\hat{z}$ direction. The EB field is determined as $B_{\text{EB}} = (B^+ + B^-)/2$, where B^+ and B^- are the values of the field where the z -component of the magnetization of the FM vanishes when the field is decreasing and increasing, respectively.

From the simulations the following qualitative results emerge. In absence of any anisotropy in the FM we observe a perpendicular coupling between FM and AFM, only at very low dilution of the latter. The magnetization reversal in the FM is by coherent rotation. The picture changes with increasing uniaxial anisotropy in the FM and upon further dilution of the AFM. The magnetization reversal in the FM is now by domain wall motion and the perpendicular coupling becomes less significant. This is because uniaxial anisotropies in both the FM and the AFM having the same axis no longer lead to an energy minimum at perpendicular coupling across the interface. Moreover AFM spins with missing AFM neighbours can lower their energy by rotating parallel to the its FM neighbour. Therefore, in the framework of our calculations a spin-flop coupling is not an important mechanism for the shift of the hysteresis loop.

Coloured pictures of typical staggered domain configurations of the bulk AFM with different anisotropies can be found in the following link: <http://www.thp.uni-duisburg.de/~arko/picture.html>. The snapshots are taken when the net magnetization of the FM is nearly zero during the decreasing field part of the hysteresis loop. As expected the domain walls are wider for smaller values of k_z , whereas Ising like domain structures are obtained for stronger anisotropies. Typical hysteresis loops for the FM and the interface monolayer of the AFM are shown in

Fig. 1. The upward shift of the hysteresis loop for the interface layer of the AFM proves the existence of remanent magnetization in the AFM domains. The magnitude of the EB field strongly depends on the amount of this upward shift.

We have calculated the EB field for a wide range of values of k_z , starting from very soft spins to rigid, Ising-like spins. Fig. 2 shows result for different thicknesses of the AFM for two values of the dilution, $p = 0.4$ and 0.6 . A logarithmic scale is used along the k_z axis only to increase the clarity of the figure. Fig. 2(a) shows that for $p = 0.4$ a thick AFM produces a peak in the EB field at an intermediate value of k_z while at lower thicknesses of the AFM the EB field increases with the anisotropy and saturates in the Ising limit. Qualitatively this can be understood as follows. The AFM domains are required to carry surplus magnetization at the interface along the $\hat{z}$ direction which must be stable during the hysteresis loop in order to produce any EB. At low values of k_z the minimum energy configuration of the AFM spins is predominantly dictated by the FM and the external field. In this limit the AFM will follow the FM, thereby producing no bias field. By increasing the anisotropy the AFM spins are forced to lie more along the z -axis and hence the bias increases. However, there exists a counter effect. Imagine a domain is formed upon field cooling which preferentially goes through defects thereby minimizing the energy. If now the anisotropy k_z is increased the domain wall width will decrease and the energy to create such a wall will increase. Thus the system will respond by flattening the domain boundaries. This reduces the probability for the domains to carry any surplus magnetization and hence the bias decreases for larger values of k_z . The compromise between these two opposite effects is achieved at some intermediate value of k_z where the bias shows a peak. However, the peak disappears at lower values of t (fig. 2(a)) or at a higher dilution (fig. 2(b)). This happens when we are close to the percolation threshold

where the domain walls pass nearly exclusively through the defects costing very little or no energy. Since no smoothening of the domain walls is required now to minimize the energy of domain formation, the second mechanism discussed above does not come into play. Hence exchange bias increases with k_z till it saturates in the Ising limit. Since the percolation threshold in three dimensions is higher than that in two dimensions, increasing the number of AFM monolayers at $p = 0.4$ we go below the threshold and the peak in the bias field reappears.

In conclusion, we find that the domain state model for EB proposed originally for the Ising AFM is not restricted to this limit. Rather under certain combination of thickness and dilution of the AFM, the softness of the AFM spins can lead to an even stronger bias field. There are several mechanisms responsible for the bias field, such as dilution, thickness and anisotropy of the AFM. Although a qualitative understanding regarding the dependence of EB on these parameters has been achieved, a quantitative study of the domain structure both at the interface and in the bulk of the AFM would provide a deeper understanding to the problem.

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Figure Captions

Fig. 1. Typical hysteresis loop along $\hat{z}$ of (a) the FM and (b) the interface monolayer of AFM, for $p = 0.6$ and $t = 2$. The net magnetization is shown in units of the saturation magnetization and the field in units of J_{FM} .

Fig. 2. Dependence of the exchange bias field, shown in units of J_{FM} , on the AFM anisotropy for (a) $p = 0.4$ and (b) $p = 0.6$ at different thicknesses.

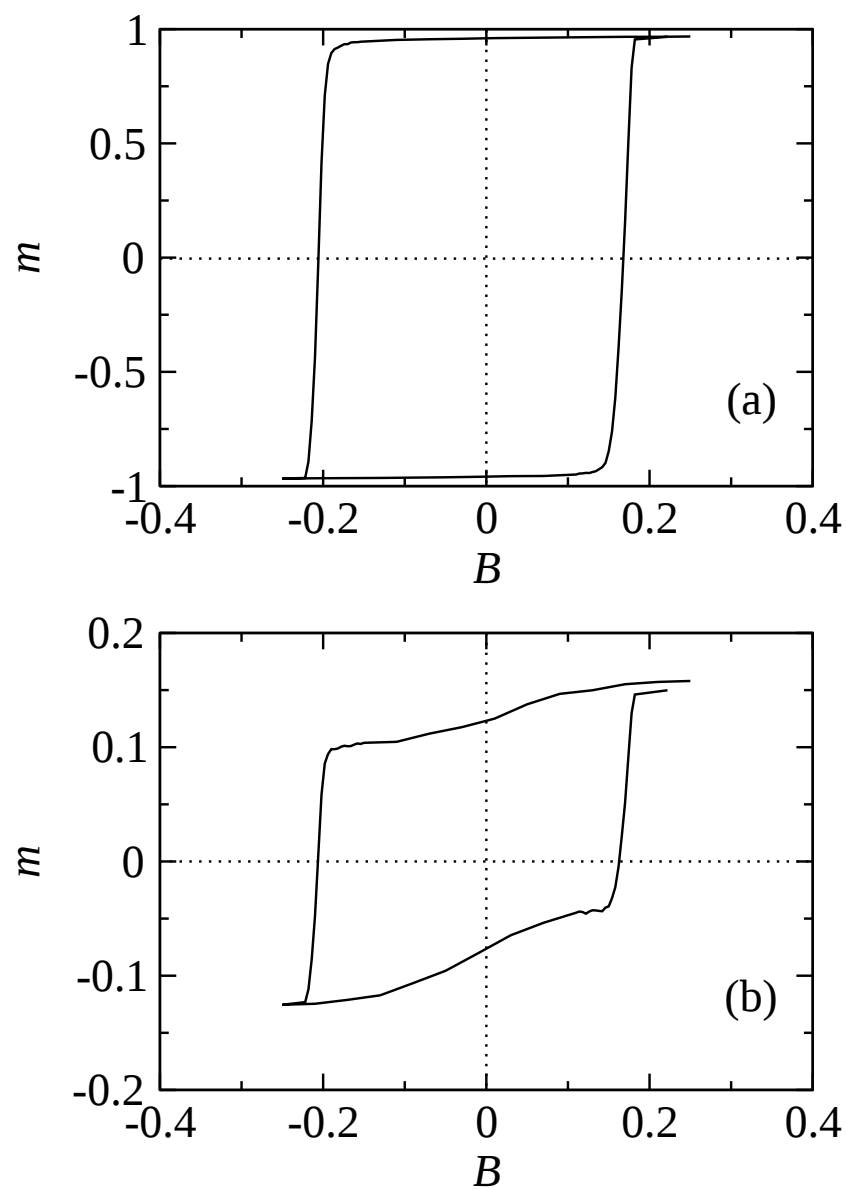


Figure 1: Misra et al.

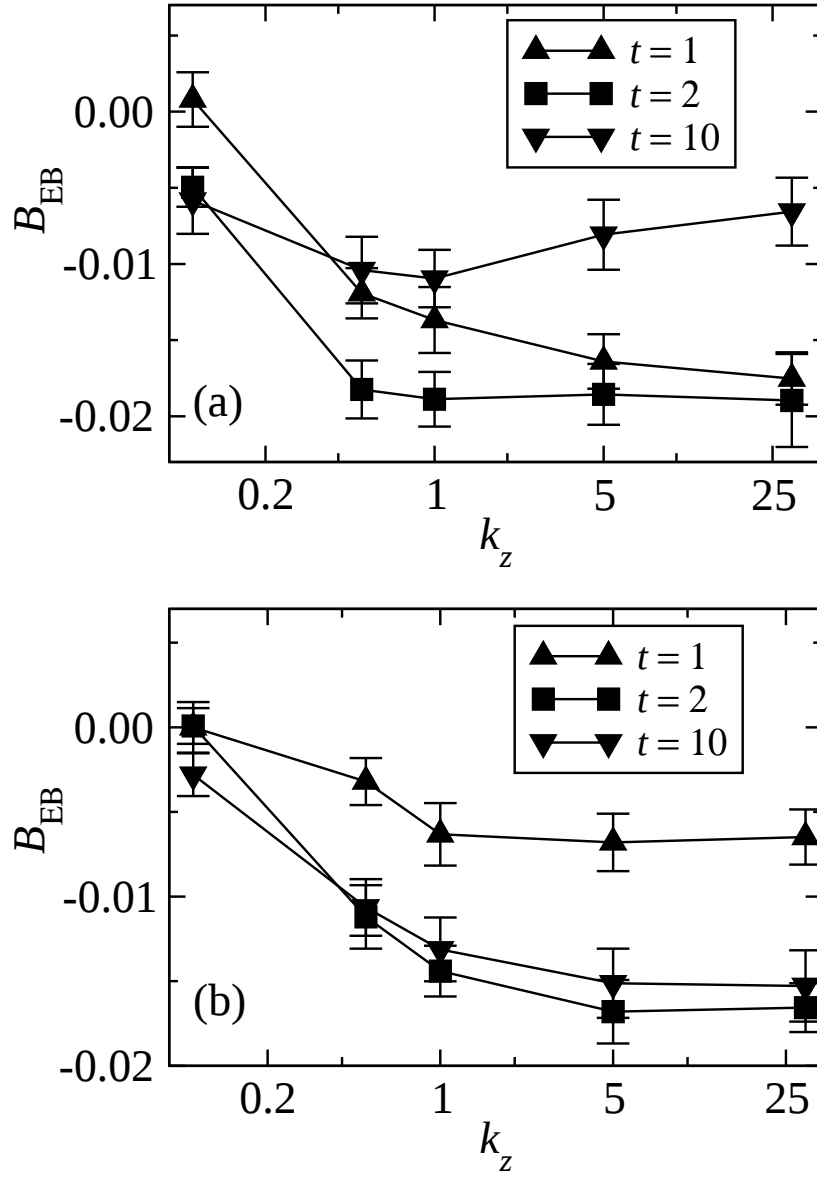


Figure 2: Misra et al.